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30V N-Channel Power MOSFET



PDFN33

Pin Definition:

Source
 Source
 Drain
 Source
 Drain

4. Gate

Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

5. Drain

Key Parameter Performance

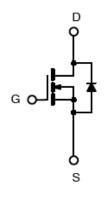
Parameter		Value	Unit	
$V_{ t DS}$		30	٧	
R _{DS(on)} (max)	V _{GS} = 10V	18		
	V _{GS} = 4.5V	28	mΩ	
Q_q		4.1	nC	

Ordering Information

Part No.	Package	Packing		
TSM180N03PQ33 RGG	PDFN33	5Kpcs / 13" Reel		

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (T_C = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Dunin Comment	T _C =25°C		25	Α
Continuous Drain Current	T _C =100°C	T _D	16	Α
Pulsed Drain Current (Note 1)		I _{DM}	I _{DM} 100	
Single Pulse Avalanche Energy (Note 2)		E _{AS}	32	mJ
Power Dissipation @ T _C = 25°C		P _D	21	W
Operating Junction Temperature		TJ	+150	°C
Storage Temperature Range		T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W	
Thermal Resistance - Junction to Case	R _{eJC}	6	°C/W	



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Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	30			V
5	$V_{GS} = 10V, I_D = 12A$	R _{DS(ON)}		14	18	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 8A$			20	28	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1.2	1.6	2.5	V
	$V_{DS} = 30V, V_{GS} = 0V$				1	μА
Zero Gate Voltage Drain Current	V _{DS} = 24V, T _J = 125°C	I _{DSS}			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 6A$	9 _{fs}		6.5		S
Dynamic						
Total Gate Charge (Note 3,4)		Q_g		4.1		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_{D} = 6A,$	Q_{gs}		1		
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	Q_{gd}		2.1		
Input Capacitance		C _{iss}		345		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C _{oss}		55		pF
Reverse Transfer Capacitance	f = 1.0MHz	C _{rss}		32		1
Switching						
Turn-On Delay Time (Note 3,4)		t _{d(on)}		2.8		
Turn-On Rise Time (Note 3,4)	$V_{DD} = 15V, I_{D} = 1A,$	t _r		7.2		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_G = 6\Omega$	t _{d(off)}		15.8		ns
Turn-Off Fall Time (Note 3,4)		t _f		4.6		1
Source-Drain Diode Ratings and Ch	aracteristic					l
Maximum Continuous Drain-Source		ı			05	_
Diode Forward Current	Integral reverse diode in	l _S			25	A
Maximum Pulse Drain-Source Diode	the MOSFET	I _{SM}			100	Α
Forward Current						
Diode-Source Forward Voltage	$V_{GS} = 0V$, $I_S = 1A$	$V_{\sf SD}$			1	V

Note:

- 1. Pulse width limited by safe operating area
- 2. L = 1mH, I_{AS} = 8A, V_{DD} = 25V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}$ C
- 3. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 4. Switching time is essentially independent of operating temperature.



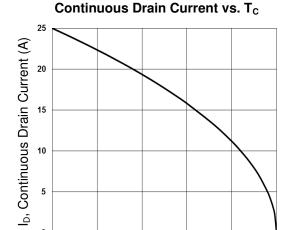
30V N-Channel Power MOSFET

Gate Charge

Pb ROHS

25

Electrical Characteristics Curve



On-Resistance vs. Junction Temperature

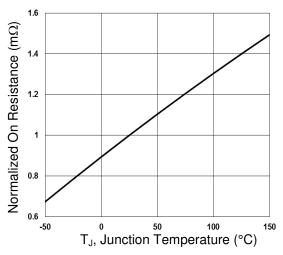
T_C, Case Temperature (°C)

100

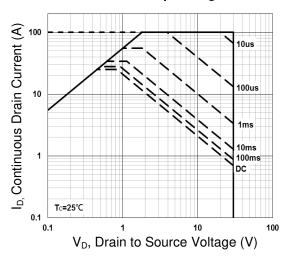
125

150

75



Maximum Safe Operating Area

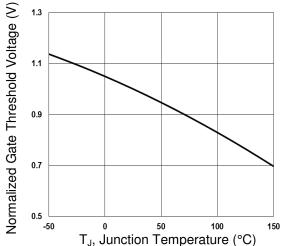


4.5 (A) (D=8A VDS=15V (D=8A) (

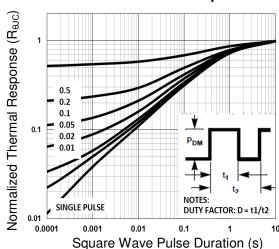
Threshold Voltage vs. Junction Temperature

Qg, Gate Charge (nC)

0



Normalized Thermal Transient Impedance Curve

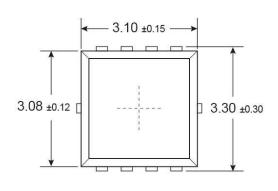


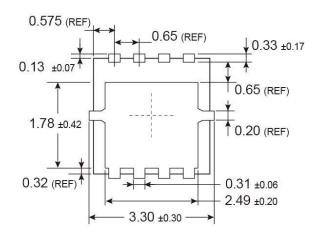


30V N-Channel Power MOSFET



PDFN33 Mechanical Drawing







Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: B1710



Pb ROHS

TSM180N03PQ33 30V N-Channel Power MOSFET

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